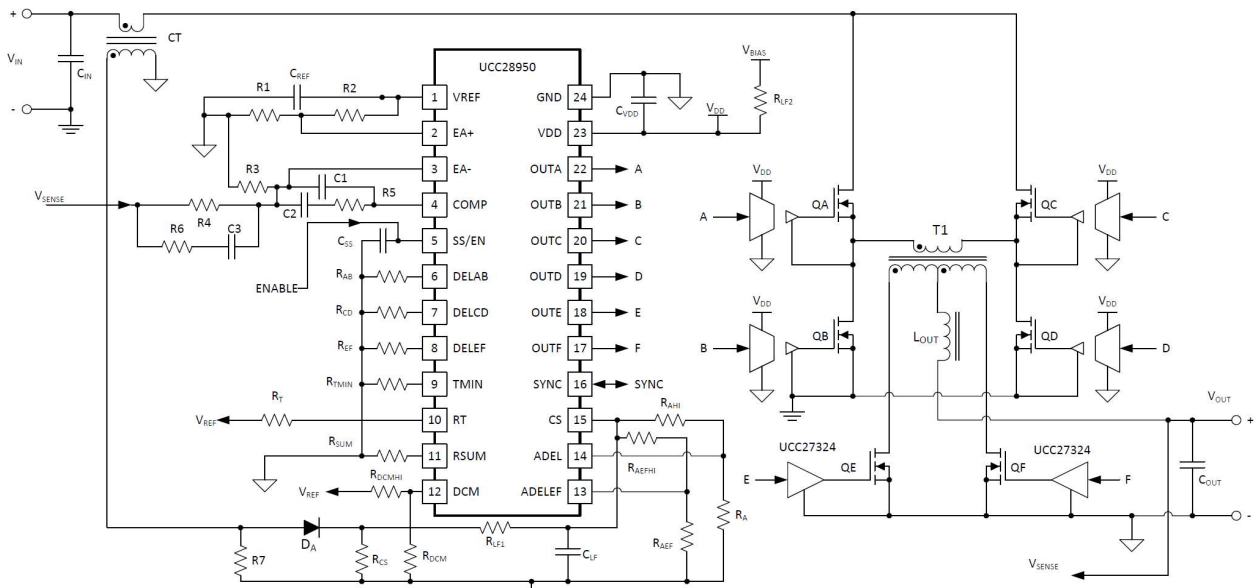


question

About dead time settings

## UCC28950 Typical Application



P19~P20

### 7.3.6 Adaptive Delay, (Delay between OUTA and OUTB, OUTC and OUTD (*DELAB*, *DELCD*, *ADEL*))

The resistor  $R_{AB}$  from the DELAB pin, DELAB to GND, along with the resistor divider  $R_{AHI}$  from CS pin to ADEL pin and  $R_A$  from ADEL pin to GND sets the delay  $T_{ABSET}$  between one of outputs OUTA or OUTB going low and the other output going high [Figure 28](#). The total resistance of this resistor divider should be in the range between 10 k $\Omega$  and 20 k $\Omega$ .

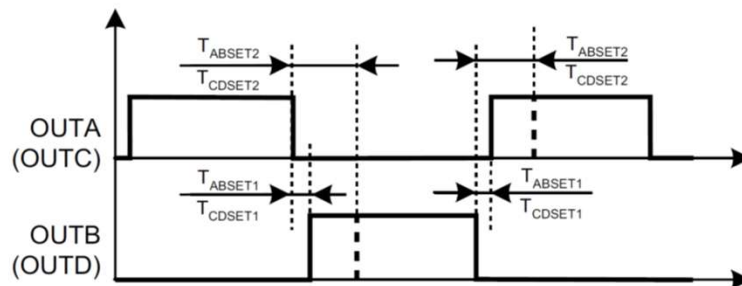


Figure 28. Delay Definitions Between OUTA and OUTB, OUTC and OUTD

This delay gradually increases as a function of the CS signal from  $T_{ABSET1}$ , which is measured at  $V_{CS} = 1.8$  V, to  $T_{ABSET2}$ , which is measured at the  $V_{CS} = 0.2$  V. This approach ensures there will be no shoot-through current during the high-side and low-side MOSFET switching and optimizes the delay for achieving ZVS condition over a wide load current range. The ratio between the longest and shortest delays is set by the resistor divider  $R_{AHI}$  and  $R_A$ . The max ratio is achieved by tying the CS and ADEL pins together. If ADEL is connected to GND, then the delay is fixed, defined only by the resistor  $R_{AB}$  from DELAB to GND. The delay  $T_{CDSET1}$  and  $T_{CDSET2}$  settings and their behaviour for outputs OUTC and OUTD are very similar to the one described for OUTA and OUTB. The difference is that resistor  $R_{CD}$  connected between DELCD pin and GND sets the delay  $T_{CDSET}$ . The ratio between the longest and shortest delays is set by the resistor divider  $R_{AHI}$  and  $R_A$ .

The delay time  $T_{ABSET}$  is defined by the following [Equation 3](#).

$$T_{ABSET} = \left( \frac{5 \times R_{AB}}{0.26 \text{ V} + CS \times K_A \times 1.3} \right) \text{ ns} \quad (3)$$

The same equation is used to define the delay time  $T_{CDSET}$  in another leg except  $R_{AB}$  is replaced by  $R_{CD}$ .

$$T_{CDSET} = \left( \frac{5 \times R_{CD}}{0.26 \text{ V} + CS \times K_A \times 1.3} \right) \text{ ns} \quad (4)$$

In these equations  $R_{AB}$  and  $R_{CD}$  are in k $\Omega$  and CS, the voltage at pin CS, is in volts and  $K_A$  is a numerical coefficient in the range from 0 to 1. The delay time  $T_{ABSET}$  and  $T_{CDSET}$  are in ns, and is measured at the IC pins. These equations are empirical and they are approximated from measured data. Thus, there is no unit agreement in the equations. As an example, assume  $R_{AB} = 15$  k $\Omega$ ,  $CS = 1$  V and  $K_A = 0.5$ . Then the  $T_{ABSET}$  will be approximately 90 ns. In both [Equation 3](#) and [Equation 4](#),  $K_A$  is the same and is defined as:

$$K_A = \frac{R_A}{R_A + R_{AHI}}$$

(5)

$K_A$  sets how the delay varies with the CS pin voltage as shown in [Figure 29](#) and [Figure 30](#).

### Feature Description (continued)

It is recommended to start by setting  $K_A = 0$  and set  $T_{ABSET}$  and  $T_{CDSET}$  relatively large using equations or plots in this data sheet to avoid hard switching or even shoot through current. The delay between outputs A, B and C, D set by resistors  $R_{AB}$  and  $R_{CS}$  accordingly. Program the optimal delays at light load first. Then by changing  $K_A$  set the optimal delay for the outputs A, B at maximum current.  $K_A$  for outputs C, D is the same as for A, D. Usually outputs C, D always have ZVS if sufficient delay is provided.

#### NOTE

The allowed resistor range on DELAB and DELCD,  $R_{AB}$  and  $R_{CD}$  is 13 kΩ to 90 kΩ.

$R_A$  and  $R_{AHI}$  define the portion of voltage at pin CS applied to the pin ADEL (See [Figure 48](#)).  $K_A$  defines how significantly the delay time depends on CS voltage.  $K_A$  varies from 0, where ADEL pin is shorted to ground ( $R_A = 0$ ) and the delay does not depend on CS voltage, to 1, where ADEL is tied to CS ( $R_{AHI} = 0$ ). Setting  $K_A$ ,  $R_{AB}$  and  $R_{CD}$  provides the ability to maintain optimal ZVS conditions of primary switches over load current because the voltage at CS pin includes the load current reflected to the primary side through the current sensing circuit. The plots in [Figure 29](#) and [Figure 30](#) show the delay time settings as a function of CS voltage and  $K_A$  for two different conditions:  $R_{AB} = R_{CD} = 13 \text{ k}\Omega$  ([Figure 29](#)) and  $R_{AB} = R_{CD} = 90 \text{ k}\Omega$  ([Figure 30](#)).

From the attached application materials,

As an example, assume  $R_{AB} = 15 \text{ k}\Omega$ ,  $CS = 1 \text{ V}$  and  $K_A = 0.5$ . In that case, it says

$T_{ABSET}$  will be about 90 ns. However, when Equation 3 is actually calculated,  $T_{ABSET} = 82.4 \text{ ns}$ , which does not match.

Also, if  $R_{AB} = R_{CD} = 15 \text{ k}\Omega$  and pin ⑭ ADEL of this IC is connected to GND,  $K_A = 0$ , so calculating Equation 3 and Equation 4 yields  $T_{ABSET} = T_{CDSET} = 288.5 \text{ ns}$ .

However, when this IC is operated and the delay time between OUTA and OUTB and between OUTC and OUTD is measured,  $T_{ABSET} = T_{CDSET} = 340 \text{ ns}$ , which do not match.

Therefore, I would like to ask you the following questions, please answer them.

- ① Is the dead time calculation method correct for the application?
- ② If it is different, please let me know how to calculate it.
- ③ If so, what is the reason for the difference between the calculated value and the measured value? Is it due to variations in parts?  
In addition, the resistance value accuracy of the setting resistor is  $\pm 0.5\%$ .
- ④ How much variation should we assume for this IC itself with respect to dead time?
- ⑤ I would like to receive information about IC variations, changes due to temperature fluctuations and aging deterioration.